

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

MCH3475 — General-Purpose Switching Device Applications

Features

- · Ultrahigh speed switching
- · 4V drive

Specifications

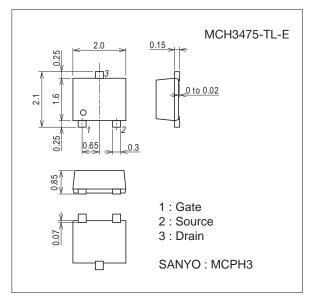
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		1.8	Α
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	7.2	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

Package Dimensions

unit : mm (typ) 7019A-003

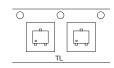


Product & Package Information

• Package : MCPH3

JEITA, JEDEC : SC-70, SOT-323
 Minimum Packing Quantity : 3,000 pcs./reel

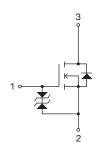
Packing Type: TL



Marking



Electrical Connection



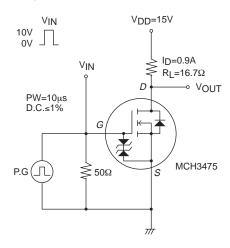
^{*} Machine Model

MCH3475

Electrical Characteristics at Ta=25°C

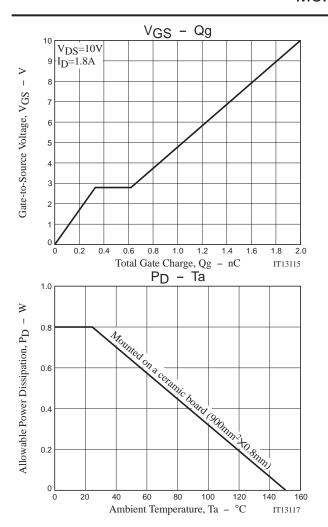
Parameter	Symbol	Conditions	Ratings			Unit
Faranteter	Symbol	Conditions	min	typ	max	Offit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =0.9A	0.66	1.1		S
Static Prain to Course On State Perintance	R _{DS} (on)1	I _D =0.9A, V _{GS} =10V		135	180	mΩ
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =0.5A, V _G S=4V		230	330	mΩ
Input Capacitance	Ciss			88		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		19		рF
Reverse Transfer Capacitance	Crss			11		рF
Turn-ON Delay Time	t _d (on)			3.4		ns
Rise Time	tr	See execified Test Circuit		3.6		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		10.5		ns
Fall Time	tf			4.0		ns
Total Gate Charge	Qg			2.0		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =1.8A		0.33		nC
Gate-to-Drain "Miller" Charge	Qgd			0.29		nC
Diode Forward Voltage	VSD	I _S =1.8A, V _G S=0V		0.86	1.2	V

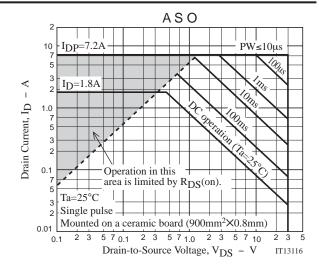
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
MCH3475-TL-E	МСРН3	3,000pcs./reel	Pb Free



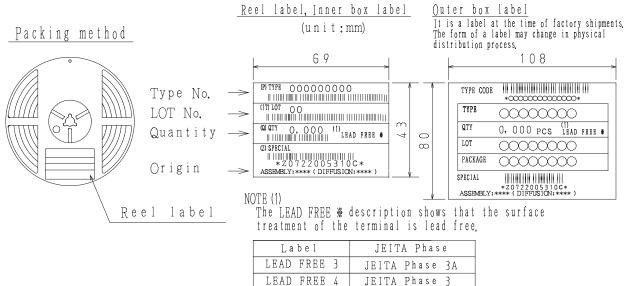


Taping Specification

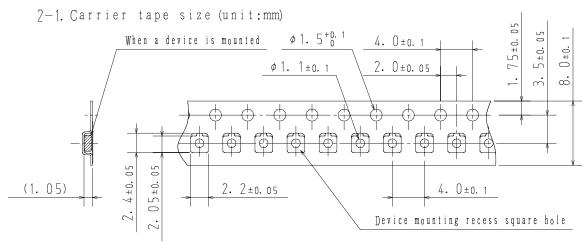
MCH3475-TL-E

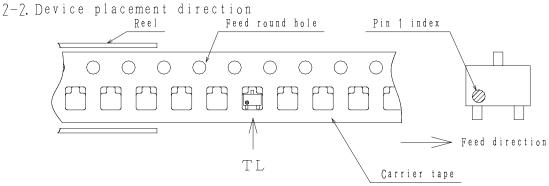
1. Packing Format

Package Name	Carrier Tape	Maximun Number of devices contained (pcs)			Packing	format
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
мсрн3	мсрн3	3,000	15, 000	90,000	5 reels contained	6 inner boxes contained
					Dimensions:mm (external)	Dimensions:mm (external)
					183×72×185	440×195×210



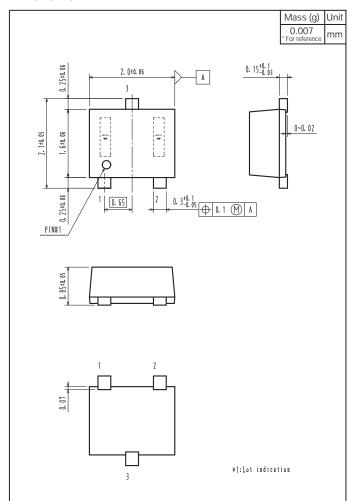
2. Taping configuration



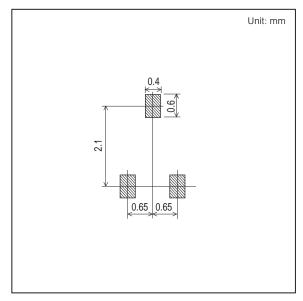


Those with pin 1 index on the feed hole side·····TL

Outline Drawing MCH3475-TL-E



Land Pattern Example



Note on usage: Since the MCH3475 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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